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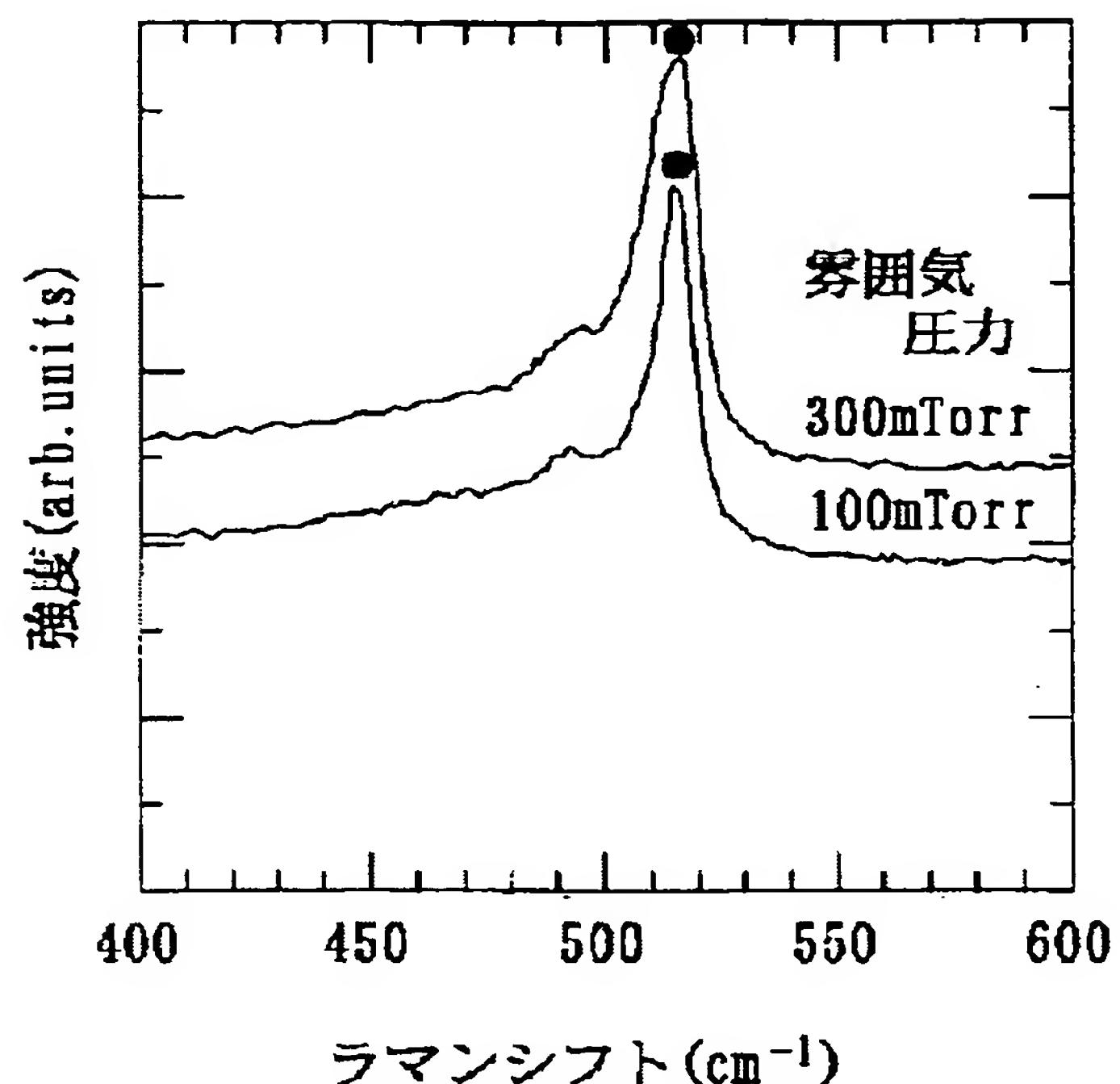
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TITLE : METHOD FOR MANUFACTURING
CRYSTALLINE SILICON FILM AND
SOLAR CELL



ABSTRACT : PROBLEM TO BE SOLVED: To provide a novel method for manufacturing a crystalline silicon film on an oxide transparent electrode, without reducing transmittivity.

SOLUTION: An amorphous silicon film is formed on an oxide transparent electrode. Atomic hydrogen is irradiated on the amorphous silicon at an atmospheric pressure of preferably 1 to 1,000 mTorr, so as to crystallize the amorphous silicon film.

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